

NTMFS0D9N03CG

MOSFET - Power, Single N-Channel, SO8-FL 30 V, 0.9 mΩ, 298 A

Features

- Advanced Package (5x6mm) with Excellent Thermal Conduction
- Ultra Low $R_{DS(on)}$ to Improve System Efficiency
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Hot Swap Application
- Power Load Switch
- Battery Management and Protection

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter		Symbol	Value	Unit	
Drain-to-Source Voltage		V_{DSS}	30	V	
Gate-to-Source Voltage		V_{GS}	± 20	V	
Continuous Drain Current $R_{\theta JC}$ (Note 2)	Steady State	$T_C = 25^\circ\text{C}$	I_D	298	A
		$T_C = 100^\circ\text{C}$		211	
Power Dissipation $R_{\theta JC}$ (Note 2)		$T_C = 25^\circ\text{C}$	P_D	144	W
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2)	Steady State	$T_A = 25^\circ\text{C}$	I_D	48	A
		$T_A = 100^\circ\text{C}$		34	
Power Dissipation $R_{\theta JA}$ (Notes 1, 2)		$T_A = 25^\circ\text{C}$	P_D	3.8	W
Pulsed Drain Current	$T_A = 25^\circ\text{C}, t_p = 10 \mu\text{s}$	I_{DM}	900	A	
Source Current (Body Diode)		I_S	120	A	
Single Pulse Drain-to-Source Avalanche Energy ($I_L = 29.2 \text{ A}_{pk}$)		E_{AS}	556	mJ	
Operating Junction and Storage Temperature		T_J, T_{STG}	-55 to +175	$^\circ\text{C}$	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T_L	260	$^\circ\text{C}$	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

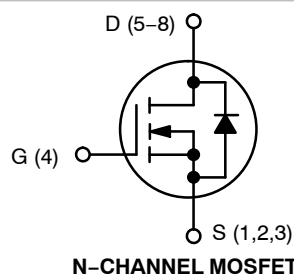
1. Surface-mounted on FR4 board using 1 in² pad, 2 oz Cu pad.
2. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.



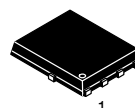
ON Semiconductor®

www.onsemi.com

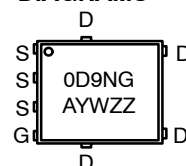
$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
30 V	0.9 mΩ @ 10 V	298 A



MARKING DIAGRAMS



SO-8 FLAT LEAD
CASE 488AA
STYLE 1



- A = Assembly Location
- Y = Year
- W = Work Week
- ZZ = Lot Traceability

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

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THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case – Steady State	$R_{\theta JC}$	1.0	°C/W
Junction-to-Ambient – Steady State (Note 3)	$R_{\theta JA}$	39	

3. Surface-mounted on FR4 board using 1 in² pad, 2 oz Cu pad.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = 250\ \mu\text{A}$, ref to 25°C		13		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 30\text{ V}$	$T_J = 25^\circ\text{C}$		1.0	μA
			$T_J = 125^\circ\text{C}$		100	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = 20\text{ V}$			100	nA

ON CHARACTERISTICS (Note 4)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 200\ \mu\text{A}$	1.3		2.2	V
Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$	$I_D = 200\ \mu\text{A}$, ref to 25°C		-5		mV/°C
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 20\text{ A}$		0.71	0.9	m Ω
Forward Transconductance	g_{FS}	$V_{DS} = 3\text{ V}, I_D = 20\text{ A}$		70		S
Gate Resistance	R_G	$T_A = 25^\circ\text{C}$		1.5		Ω

CHARGES AND CAPACITANCES

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, V_{DS} = 15\text{ V}, f = 1\text{ MHz}$		9550		pF
Output Capacitance	C_{OSS}			4306		
Reverse Transfer Capacitance	C_{RSS}			243		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 10\text{ V}, V_{DS} = 15\text{ V}; I_D = 20\text{ A}$		131.4		nC
Threshold Gate Charge	$Q_{G(TH)}$			14.2		
Gate-to-Source Charge	Q_{GS}			24.2		
Gate-to-Drain Charge	Q_{GD}			13.5		

SWITCHING CHARACTERISTICS (Note 5)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 10\text{ V}, V_{DS} = 15\text{ V}, I_D = 20\text{ A}, R_G = 3.0\ \Omega$		20		ns
Rise Time	t_r			16		
Turn-Off Delay Time	$t_{d(OFF)}$			93		
Fall Time	t_f			24		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = 10\text{ A}$	$T_J = 25^\circ\text{C}$	0.75	1.2	V
			$T_J = 125^\circ\text{C}$	0.60		
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s}, V_{DS} = 15\text{ V}, I_S = 20\text{ A}$		83		ns
Reverse Recovery Charge	Q_{RR}			114		nC

4. Pulse Test: pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

5. Switching characteristics are independent of operating junction temperatures.

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TYPICAL CHARACTERISTICS

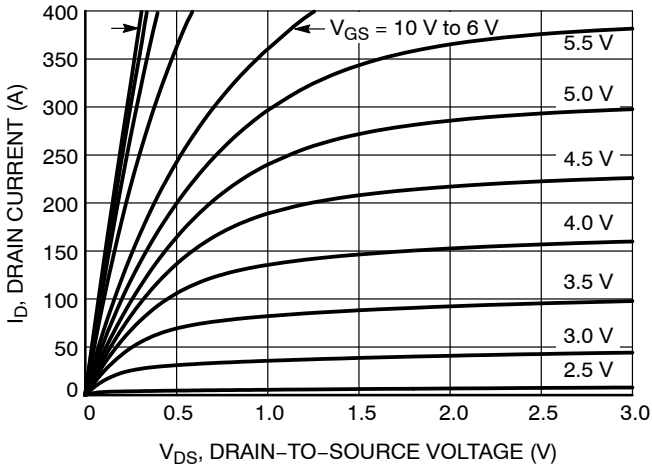


Figure 1. On-Region Characteristics

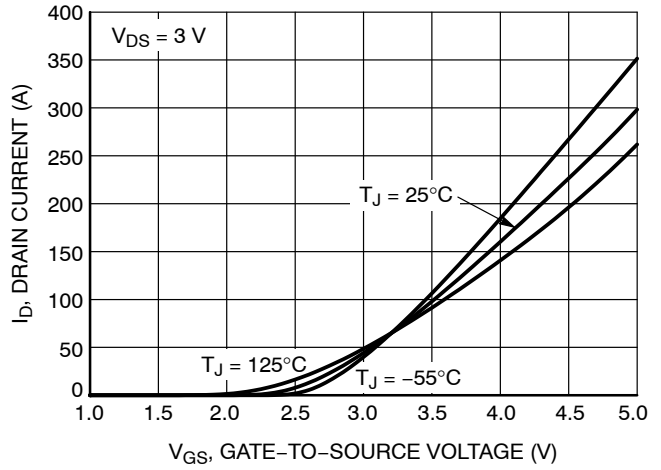


Figure 2. Transfer Characteristics

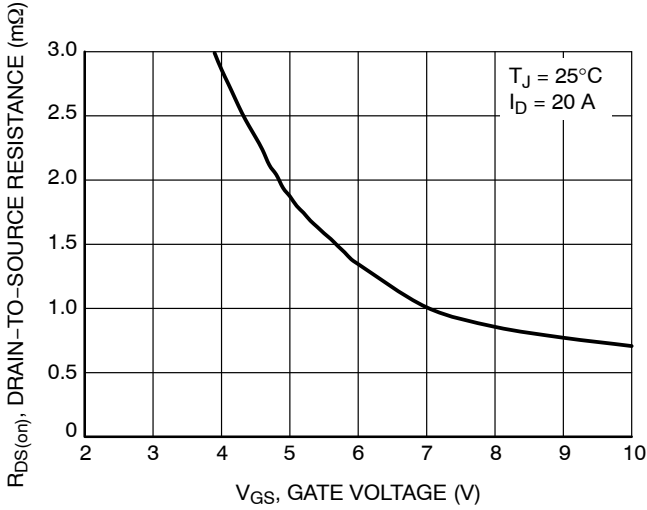


Figure 3. On-Resistance vs. Gate-to-Source Voltage

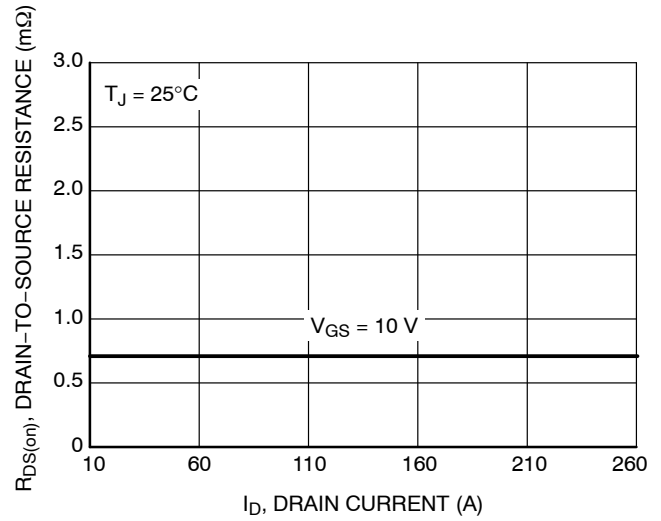


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

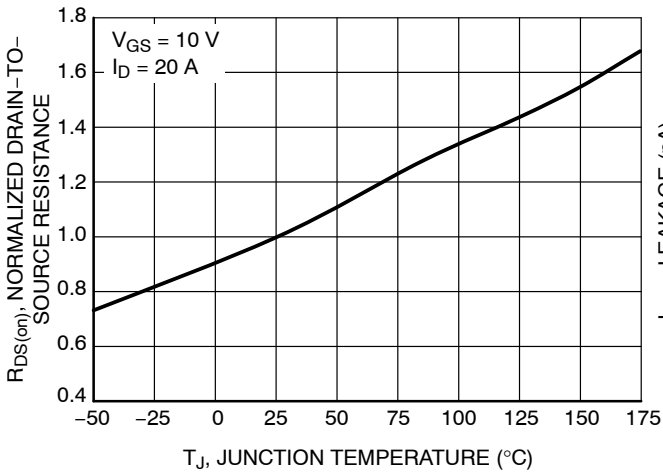


Figure 5. On-Resistance Variation with Temperature

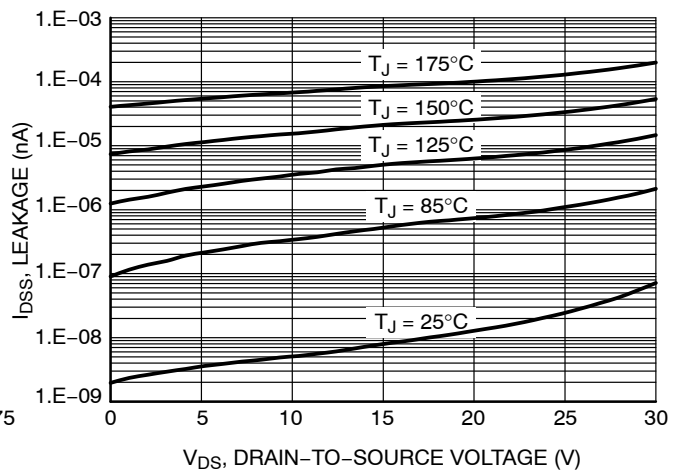


Figure 6. Drain-to-Source Leakage Current vs. Voltage

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TYPICAL CHARACTERISTICS

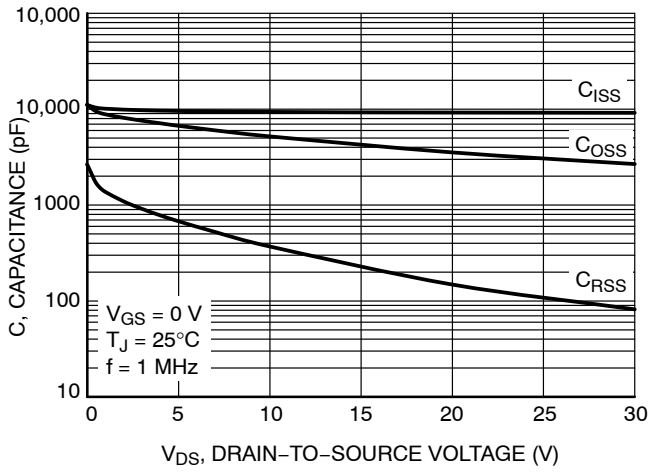


Figure 7. Capacitance Variation

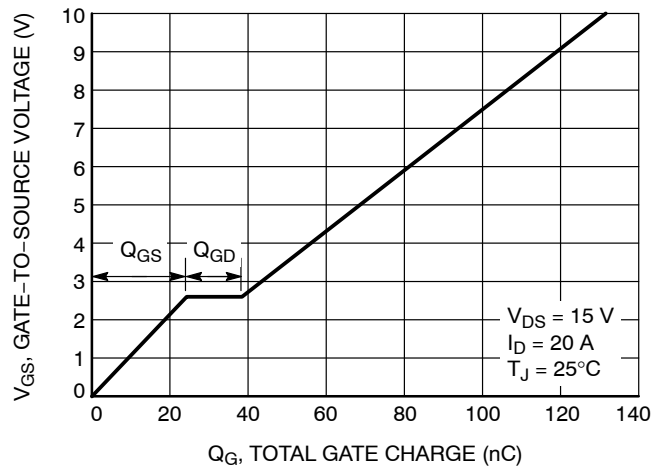


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

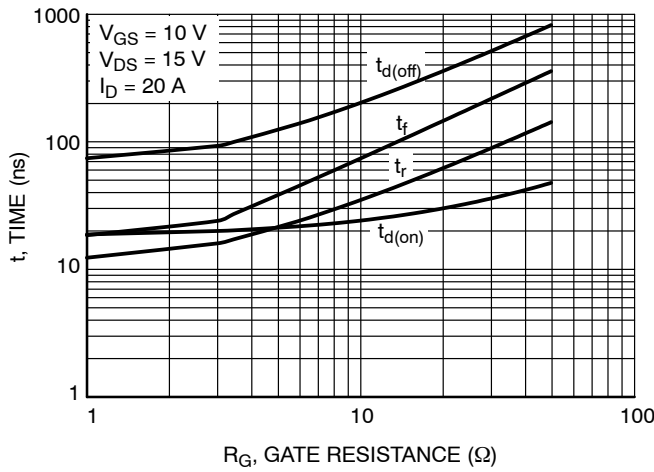


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

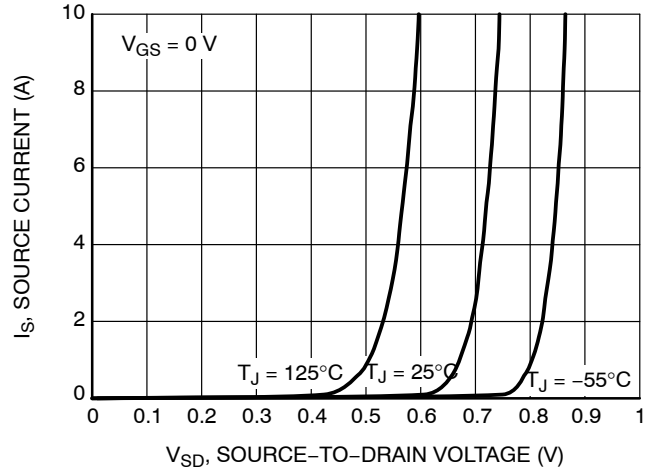


Figure 10. Diode Forward Voltage vs. Current

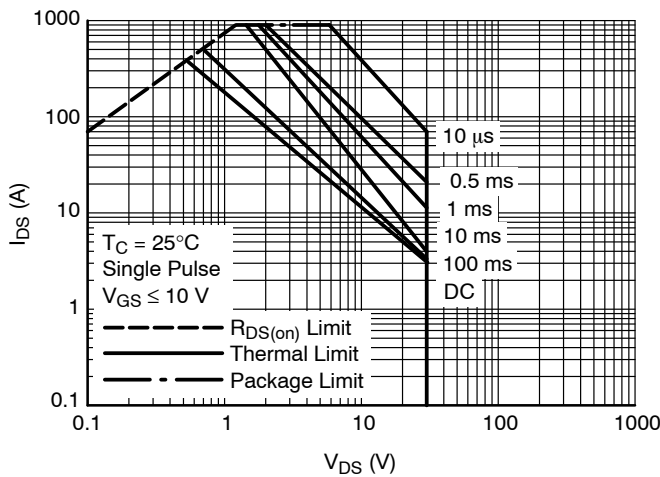


Figure 11. Safe Operating Area

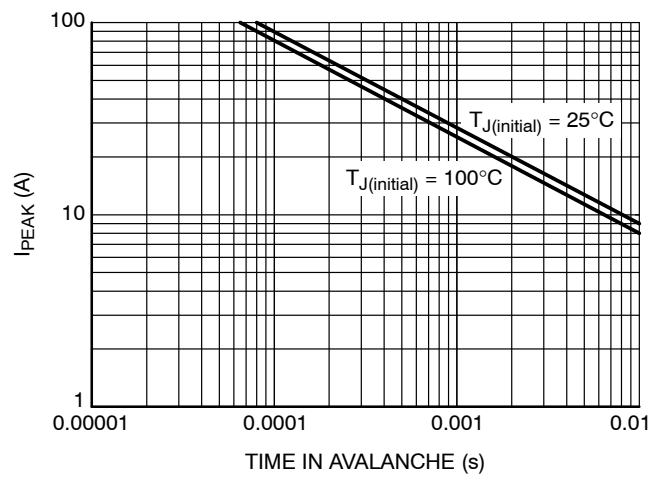


Figure 12. IPEAK vs. Time in Avalanche

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TYPICAL CHARACTERISTICS

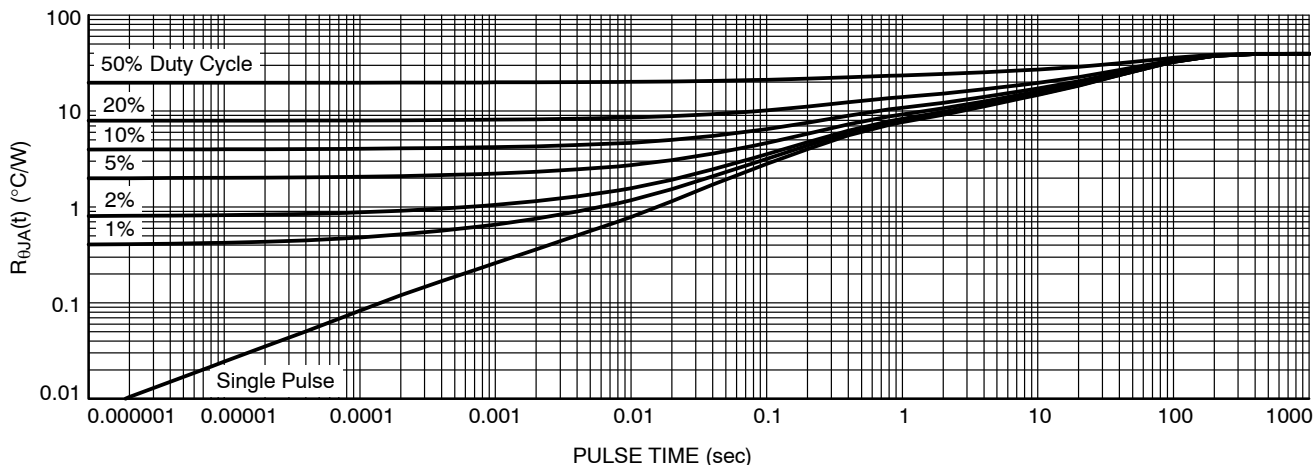


Figure 13. Thermal Characteristics

DEVICE ORDERING INFORMATION

Device	Marking	Package	Shipping†
NTMFS0D9N03CGT1G	0D9NG	DFN5 (Pb-Free)	1500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

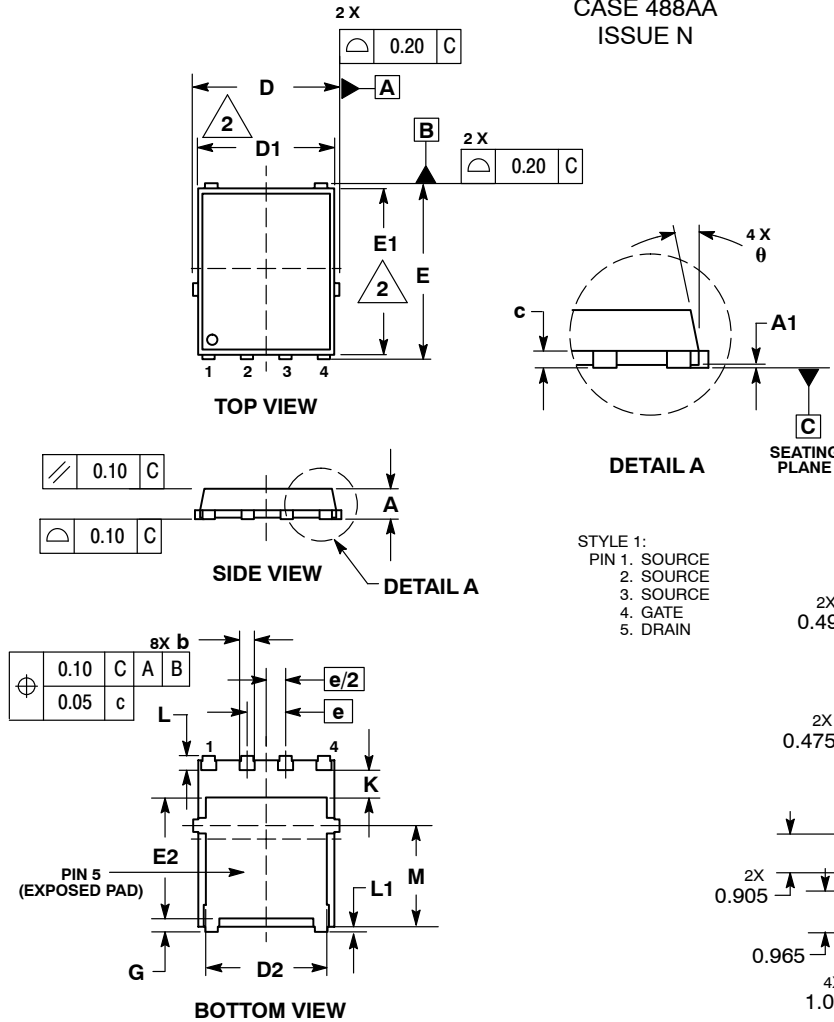
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PACKAGE DIMENSIONS

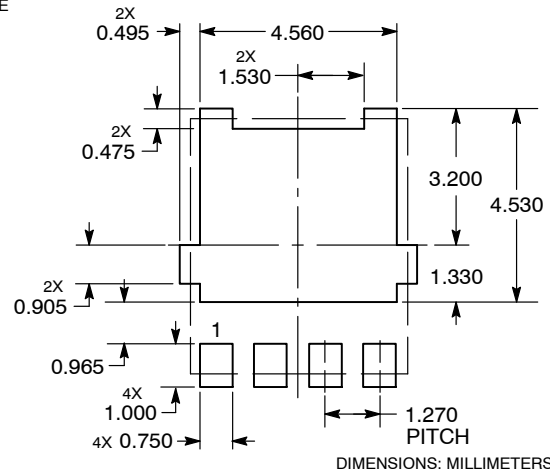
DFN5 5x6, 1.27P
(SO-8FL)
CASE 488AA
ISSUE N

- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.00	---	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
e	1.27 BSC		
G	0.51	0.575	0.71
K	1.20	1.35	1.50
L	0.51	0.575	0.71
L1	0.125 REF		
M	3.00	3.40	3.80
θ	0°	---	12°



RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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